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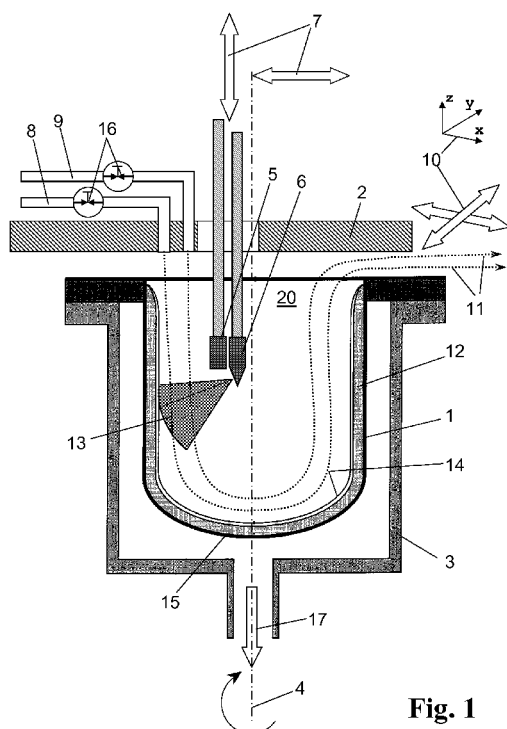


Fig. 1

(57) Abstract: The invention starts from a method for producing a crucible of quartz glass in that SiO₂ inner layer granules are vitrified in a rotating melting mold (1), which is covered at least in part by a heat shield (2), in a light gas-containing atmosphere under the action of a plasma to obtain a transparent inner layer, at least part of the light gas being supplied to the melting mold (1) through a gas inlet (8,9) of the heat shield. In order to form an inner layer with a particularly low bubble content and with minimal efforts in terms of energy and material, it is proposed that in a layer-forming step preceding the vitrifying step, a granule layer (14) of the SiO₂ inner layer granules is formed on the inner wall, and wherein the plasma zone (13) and the heat shield (2) together with the gas inlet (8,9) are movable at least in a direction perpendicular to the rotation axis and are moved laterally in the direction of the granule layer (14) during the vitrifying step so as to vitrify the granule layer (14).

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